

Supplementary material

Growth rate determined for each material. Figure S1a u-SnO₂ and CdS and Figure S1b CdTe. All the experiments were carried out in Ar atmosphere; the substrate temperature and RF-power were fixed at 250 °C and 80 W, respectively.

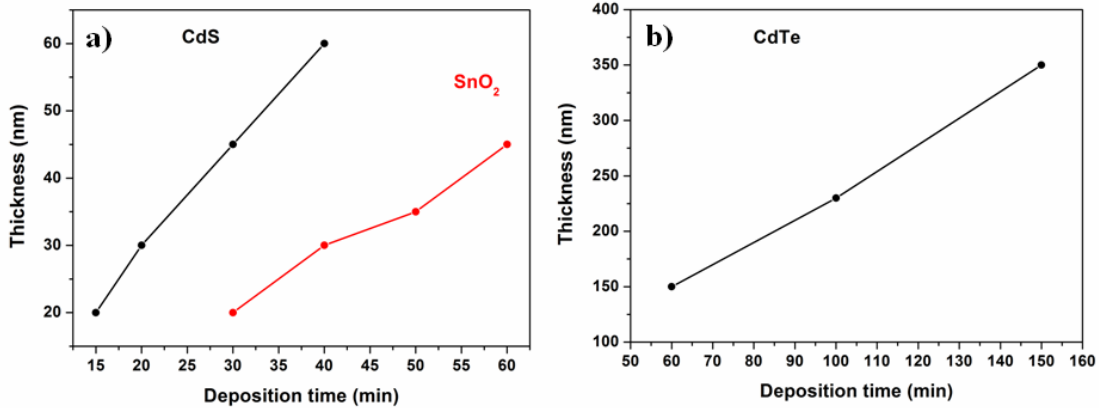


Figure S1. Growth rate determined for each material. (a) u-SnO₂ and CdS and (b) CdTe.

The transmission spectra were not appreciably modified by the insertion of the buffer layer. This was expected given the transparency of the u-SnO₂ layer. Figure S2 shows the transmission spectra for the CdTe layer and the heterostructures with and without buffer layer studied in this paper.

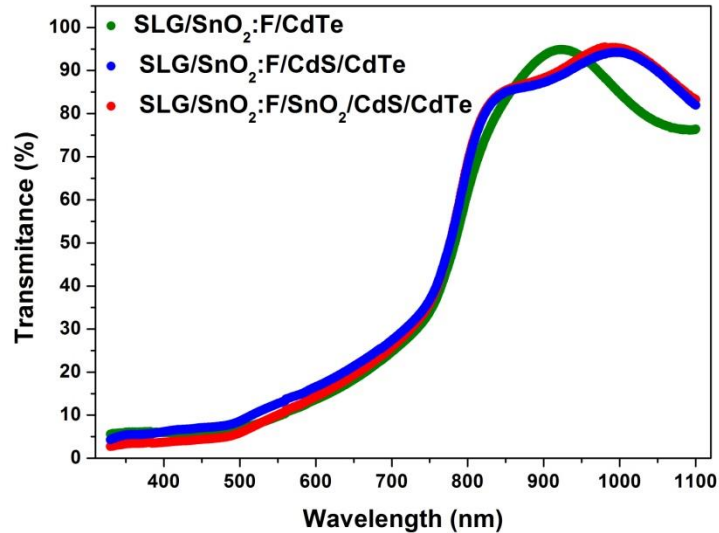


Figure S2. Transmission spectra for the CdTe layer and the heterostructures with and without buffer layer studied in this paper.

Figure S3 shows the statistics on the in-plane grain sizes in each layer. A total of 200 grains were measured and a histogram was created from the data. The data were adjusted with a Gaussian shape.

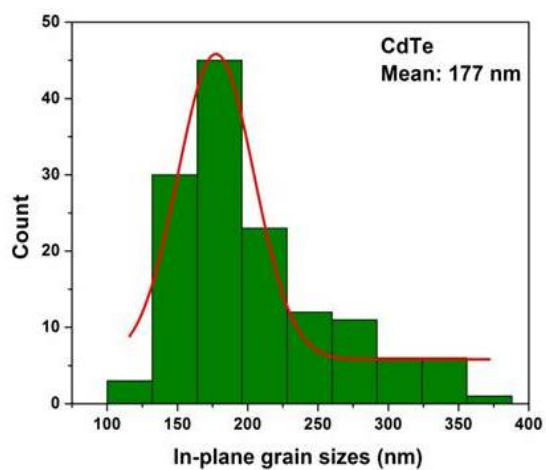
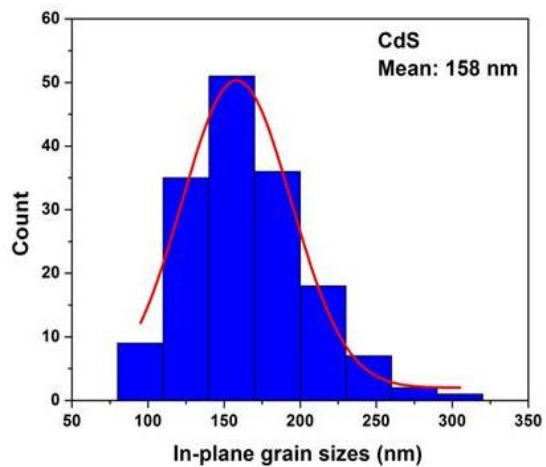
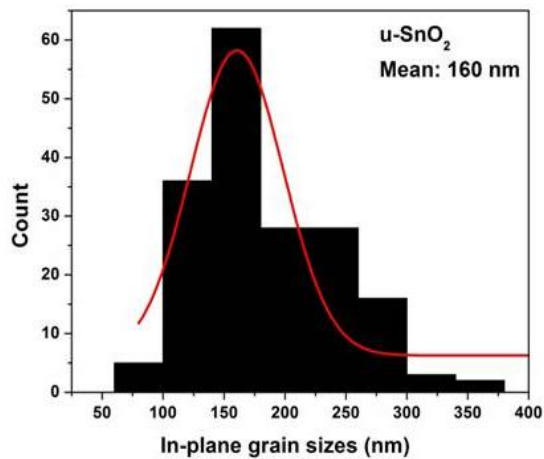


Figure S3. Histograms of the grain size values in each layer.